

isc Silicon NPN Power Transistors

BUP23B/C

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 400V$ (Min)-BUP23B
450V (Min)-BUP23C
- High Switching Speed

APPLICATIONS

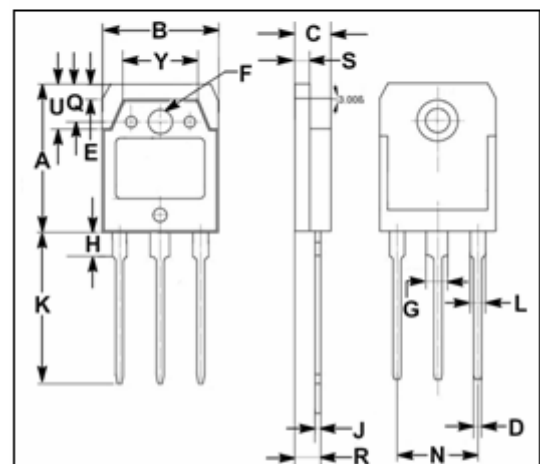
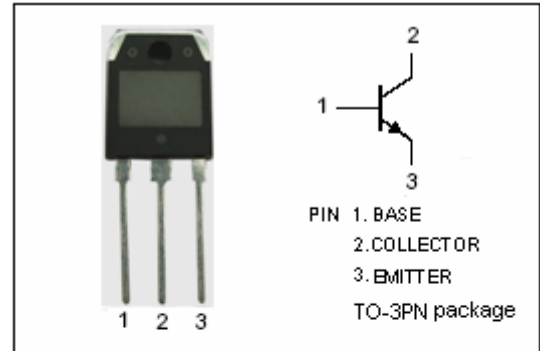
- Designed for use in converters, inverters, switching regulators, motor control systems etc.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT	
V_{CES}	Collector- Emitter Voltage($V_{BE} = 0$)	BUP23B	750	V
		BUP23C	850	
V_{CEO}	Collector-Emitter Voltage	BUP23B	400	V
		BUP23C	450	
V_{EBO}	Emitter-Base Voltage	9	V	
I_C	Collector Current- Continuous	15	A	
I_{CM}	Collector Current-Peak	30	A	
I_B	Base Current- Continuous	6	A	
I_{BM}	Base Current-Peak	9	A	
P_C	Collector Power Dissipation @ $T_C=25^\circ C$	125	W	
T_J	Junction Temperature	150	$^\circ C$	
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	0.7	$^\circ C/W$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.10
H	3.20	3.40
J	0.595	0.605
K	20.50	20.70
L	1.90	2.10
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	BUP23B	400			V
		BUP23C				
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	BUP23B			1.5	V
		BUP23C			1.5	
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	BUP23B			1.5	V
		BUP23C			1.5	
I_{CES}	Collector Cutoff Current	$V_{CE}=V_{CESmax}; V_{BE}=0$			1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=9V; I_C=0$			10	mA
h_{FE}	DC Current Gain	$I_C=1A; V_{CE}=5V$		25		

Switching Times, Resistive Load

t_{on}	Turn-On Time	For BUP23B $I_C=10A; I_{B1} = I_{B2} =1.33A$ For BUP23C $I_C=10A; I_{B1} = I_{B2} =1.67A$		0.7		μs
t_{stg}	Storage Time			2.0		μs
t_f	Fall Time			0.27		μs